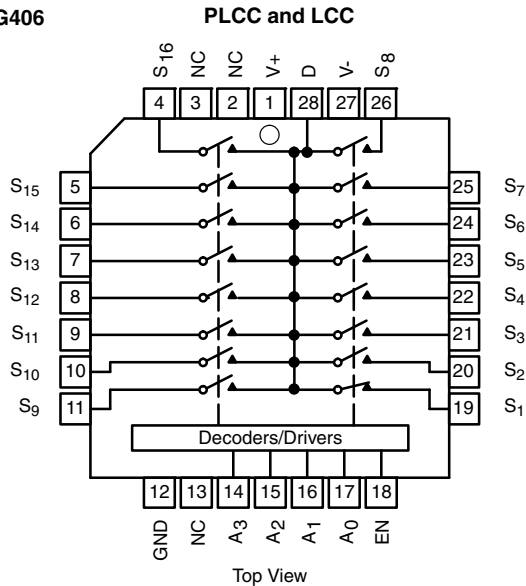
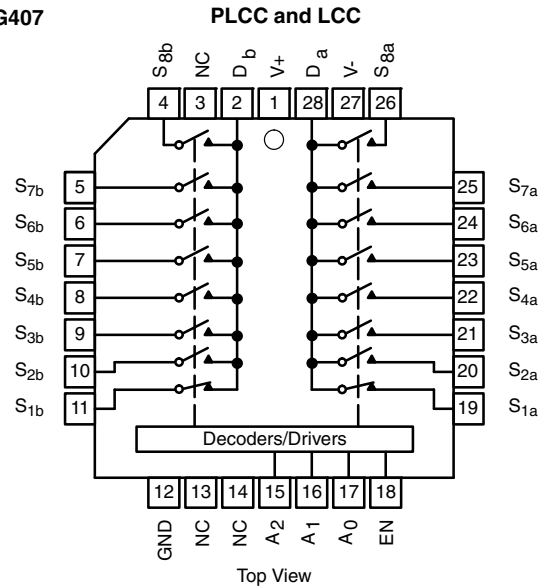


FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION

DG406



DG407



TRUTH TABLE (DG406)					
A ₃	A ₂	A ₁	A ₀	EN	ON SWITCH
X	X	X	X	0	None
0	0	0	0	1	1
0	0	0	1	1	2
0	0	1	0	1	3
0	0	1	1	1	4
0	1	0	0	1	5
0	1	0	1	1	6
0	1	1	0	1	7
0	1	1	1	1	8
1	0	0	0	1	9
1	0	0	1	1	10
1	0	1	0	1	11
1	0	1	1	1	12
1	1	0	0	1	13
1	1	0	1	1	14
1	1	1	0	1	15
1	1	1	1	1	16

TRUTH TABLE (DG407)				
A ₂	A ₁	A ₀	EN	ON SWITCH PAIR
X	X	X	0	None
0	0	0	1	1
0	0	1	1	2
0	1	0	1	3
0	1	1	1	4
1	0	0	1	5
1	0	1	1	6
1	1	0	1	7
1	1	1	1	8

Notes

- Logic "0" = V_{AL} ≤ 0.8 V
- Logic "1" = V_{AH} ≥ 2.4 V
- X = Do not Care

ORDERING INFORMATION (DG406)		
TEMP. RANGE	PACKAGE	PART NUMBER
-40 °C to 85 °C	28-Pin Plastic DIP	DG406DJ, DG406DJ-E3
	28-Pin PLCC	DG406DN, DG406DN-T1-E3
	28-Pin Widebody SOIC	DG406DW, DG406DW-E3, DG406DW-T1-E3

ORDERING INFORMATION (DG407)		
TEMP. RANGE	PACKAGE	PART NUMBER
-40 °C to 85 °C	28-Pin Plastic DIP	DG407DJ, DG407DJ-E3
	28-Pin PLCC	DG407DN, DG407DN-T1-E3
	28-Pin Widebody SOIC	DG407DW, DG407DW-E3, DG407DW-T1-E3

Note

- -T1 indicates Tape and Reel, -E3 indicates Lead-Free and RoHS Compliant, NO -E3 indicates standard Tin/Lead finish.



ABSOLUTE MAXIMUM RATINGS			
PARAMETER		LIMIT	UNIT
Voltages Referenced to V-	V+ to V - ^f	44	V
	GND to V-	-25	
Digital Inputs ^a , V _S , V _D		(V-) - 2 to (V+) + 2 V or 20 mA, whichever occurs first	
Current (Any terminal)		30	mA
Peak Current, S or D (Pulsed at 1 ms, 10 % duty cycle max.)		100	
Storage Temperature	(AK, AZ Suffix)	-65 to 150	°C
	(DJ, DN Suffix)	-65 to 125	
Power Dissipation (Package) ^b	28-Pin Plastic DIP ^b	625	mW
	28-Pin Plastic PLCC ^c	450	
	28-Pin Widebody SOIC	450	

Notes

- a. Signals on SX, DX or INX exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads soldered or welded to PC board.
- c. Derate 6 mW/°C above 75 °C.
- d. Derate 12 mW/°C above 75 °C.
- e. Derate 13.5 mW/°C above 75 °C.
- f. Also applies when V- = GND



SPECIFICATIONS ^a								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V ₊ = 15 V, V ₋ = -15 V V _{AL} = 0.8 V, V _{AH} = 2.4 V ^f	TEMP. ^b	TYP. ^c	D SUFFIX -40 °C TO 85 °C		UNIT	
					MIN. ^d	MAX. ^d		
Analog Switch								
Analog Signal Range ^e	V _{ANALOG}		Full	-	-15	15	V	
Drain-Source On-Resistance	R _{DS(on)}	V _D = ± 10 V, I _S = -10 mA sequence each switch on	Room	50	-	100	Ω	
			Full	50	-	125		
R _{DS(on)} Matching Between Channels ^g	ΔR _{DS(on)}	V _D = ± 10 V	Room	5	-	-	%	
Source Off Leakage Current	I _{S(off)}		Room	0.01	-0.5	0.5	nA	
			Full	0.01	-5	5		
Drain Off Leakage Current	I _{D(off)}	V _{EN} = 0 V V _D = ± 10 V V _S = ± 10 V	DG406	Room	0.04	-1		1
			DG406	Full	0.04	-40		40
			DG407	Room	0.04	-1		1
			DG407	Full	0.04	-20		20
Drain On Leakage Current	I _{D(on)}	V _S = V _D = ± 10 sequence each switch on	DG406	Room	0.04	-1		1
			DG406	Full	0.04	-40		40
			DG407	Room	0.04	-1	1	
			DG407	Full	0.04	-20	20	
Digital Control								
Logic High Input Voltage	V _{INH}		Full	-	2.4	-	V	
Logic Low Input Voltage	V _{INL}		Full	-	-	0.8		
Logic High Input Current	I _{AH}	V _A = 2.4 V, 15 V	Full	-	-1	1	μA	
Logic Low Input Current	I _{AL}	V _{EN} = 0 V, 2.4 V, V _A = 0 V	Full	-	-1	1		
Logic Input Capacitance	C _{in}	f = 1 MHz	Room	7	-	-	pF	
Dynamic Characteristics								
Transition Time	t _{TRANS}	see figure 2	Room	200	-	350	ns	
			Full	-	-	450		
Break-Before-Make Interval	t _{OPEN}	see figure 4	Room	50	25	-		
			Full	-	10	-		
Enable Turn-On Time	t _{ON(EN)}	see figure 3	Room	150	-	200		
			Full	-	-	400		
Enable Turn-Off Time	t _{OFF(EN)}		Room	70	-	150		
			Full	-	-	300		
Charge Injection	Q	V _S = 0 V, C _L = 1 nF, R _S = 0 Ω	Room	15	-	-	pC	
Off Isolation ^h	OIRR	V _{EN} = 0 V, R _L = 1 kΩ f = 100 kHz	Room	-69	-	-	dB	
Source Off Capacitance	C _{S(off)}	V _{EN} = 0 V, V _S = 0 V, f = 1 MHz	Room	8	-	-	pF	
Drain Off Capacitance	C _{D(off)}	V _{EN} = 0 V V _D = 0 V f = 1 MHz	Room	130	-	-		
			DG407	Room	65	-		-
Drain On Capacitance	C _{D(on)}		DG406	Room	140	-		-
			DG407	Room	70	-		-
Power Supplies								
Positive Supply Current	I ₊	V _{EN} = V _A = 0 or 5 V	Room	13	-	30	μA	
			Full	-	-	75		
Negative Supply Current	I ₋		Room	-0.01	-1	-		
			Full	-	-10	-		
Positive Supply Current	I ₊	V _{EN} = 2.4 V, V _A = 0 V	Room	50	-	500		
			Full	-	-	700		
Negative Supply Current	I ₋		Room	-0.01	-20	-		
			Full	-0.01	-20	-		



SPECIFICATIONS _a (for Single Supply)								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V ₊ = 12 V, V ₋ = 0 V V _{AL} = 0.8 V, V _{AH} = 2.4 V ^f	TEMP. ^b	TYP. ^c	D SUFFIX -40 °C TO 85 °C		UNIT	
					MIN. ^d	MAX. ^d		
Analog Switch								
Analog Signal Range ^e	V _{ANALOG}		Full	-	0	12	V	
Drain-Source On-Resistance	R _{DS(on)}	V _D = 3 V, 10 V, I _S = -1 mA sequence each switch on	Room	90	-	120	Ω	
R _{DS(on)} Matching Between Channels ^g	ΔR _{DS(on)}		Room	5	-	-	%	
Source Off Leakage Current	I _{S(off)}	V _{EN} = 0 V V _D = 10 V or 0.5 V V _S = 0.5 V or 10 V	Room	0.01	-	-	nA	
Drain Off Leakage Current	I _{D(off)}		DG406	Room	0.04	-		-
			DG407	Room	0.04	-		-
Drain On Leakage Current	I _{D(on)}		DG406	Room	0.04	-		-
		DG407	Room	0.04	-	-		
Dynamic Characteristics								
Switching Time of Multiplexer	t _{OPEN}	V _{S1} = 8 V, V _{S8} = 0 V, V _{IN} = 2.4 V	Room	300	-	450	ns	
Enable Turn-On Time	t _{ON(EN)}	V _{INH} = 2.4 V, V _{INL} = 0 V V _{S1} = 5 V	Room	250	-	600		
Enable Turn-Off Time	t _{OFF(EN)}		Room	150	-	300		
Charge Injection	Q	C _L = 1 nF, V _S = 6 V, R _S = 0	Room	20	-	-	pC	
Power Supplies								
Positive Supply Current	I ₊	V _{EN} = 0 V or 5 V, V _A = 0 V or 5 V	Room	13	-	30	μA	
			Full	-	-	75		
Negative Supply Current	I ₋		Room	-0.01	-20	-		
			Full	-0.01	-20	-		

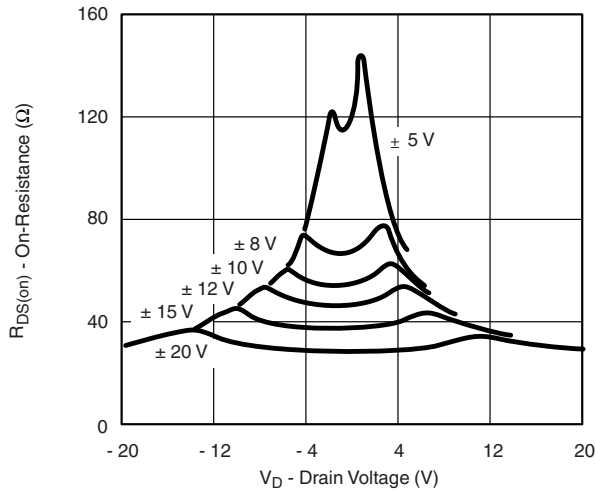
Notes

- a. Refer to PROCESS OPTION FLOWCHART.
- b. Room = 25 °C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e. Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.
- g. ΔR_{DS(on)} = R_{DS(on)} max. - R_{DS(on)} min.
- h. Worst case isolation occurs on Channel 4 due to proximity to the drain pin.

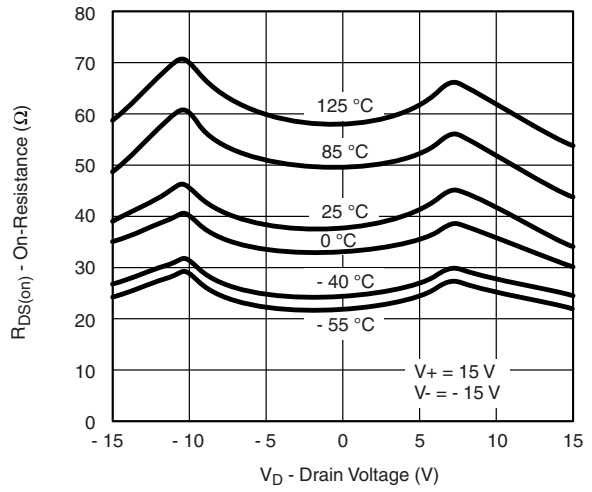
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



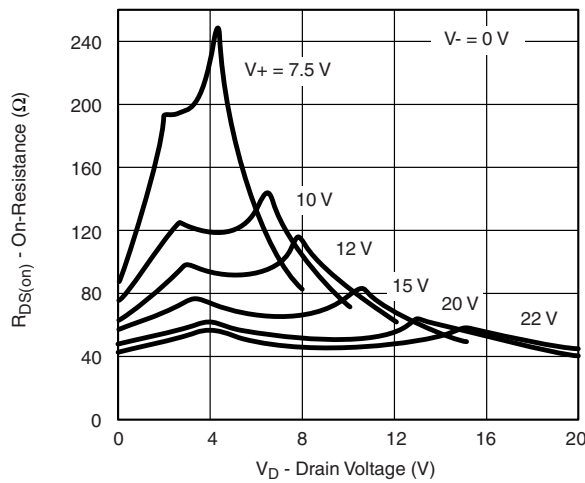
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



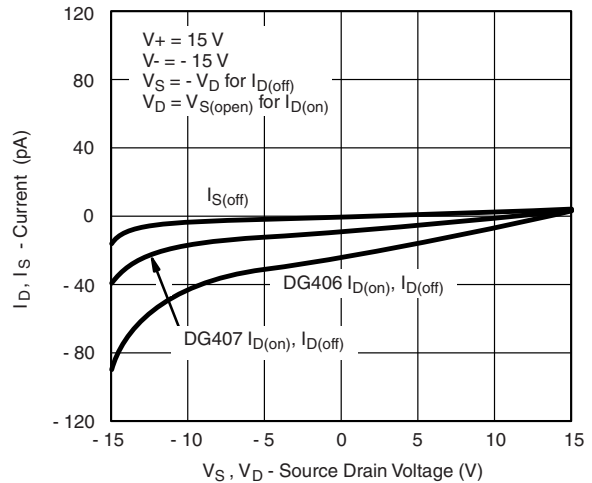
R_{DS(on)} vs. V_D and Supply



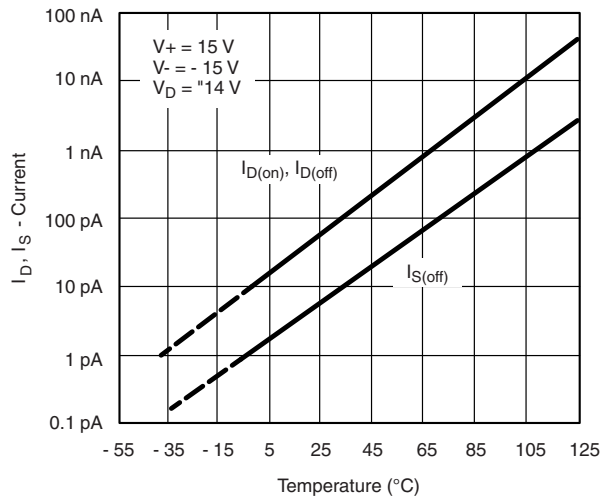
R_{DS(on)} vs. V_D and Temperature



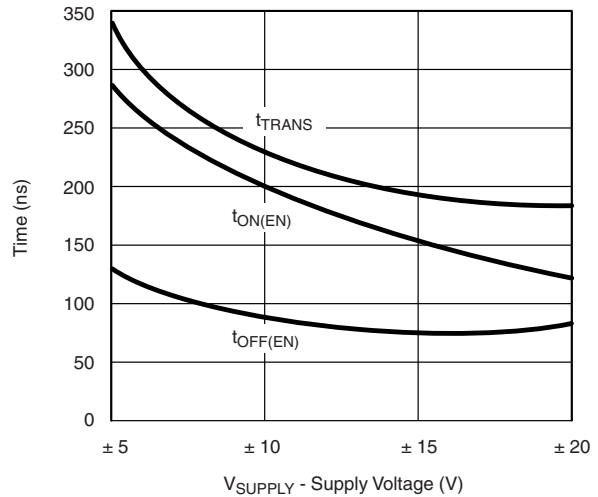
R_{DS(on)} vs. V_D and Supply



I_D, I_S Leakage Currents vs. Analog Voltage



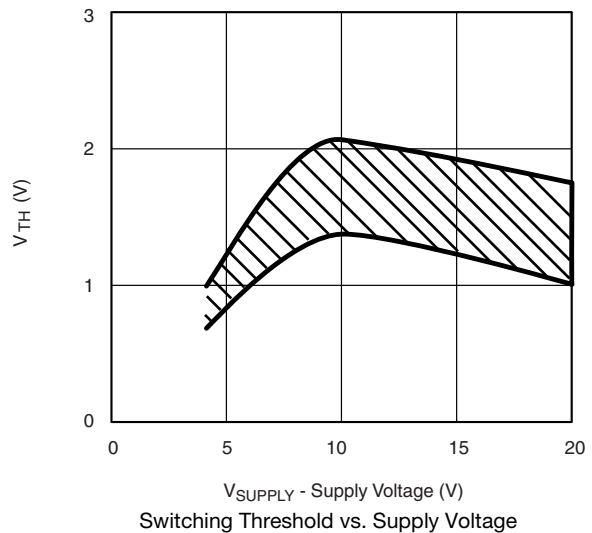
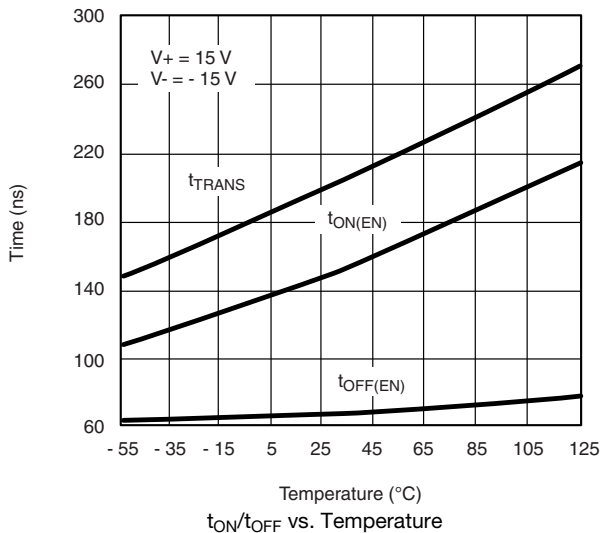
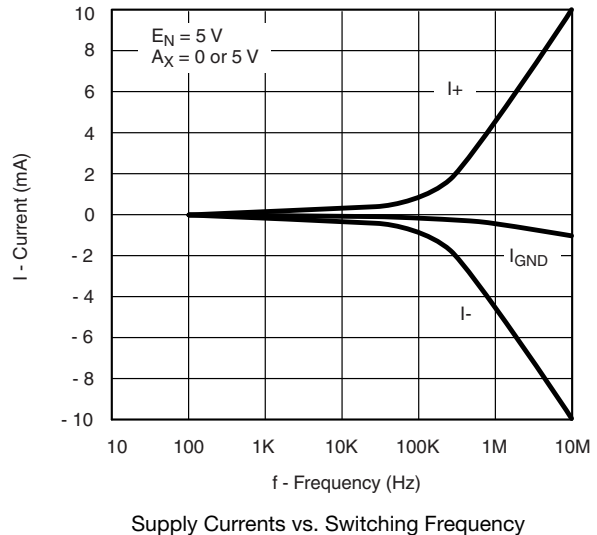
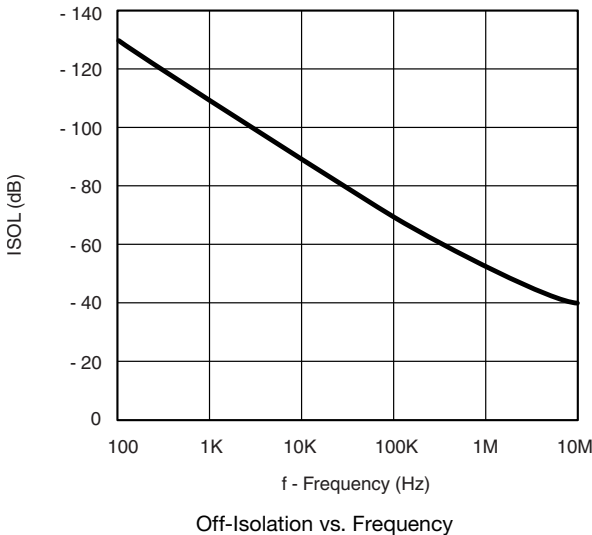
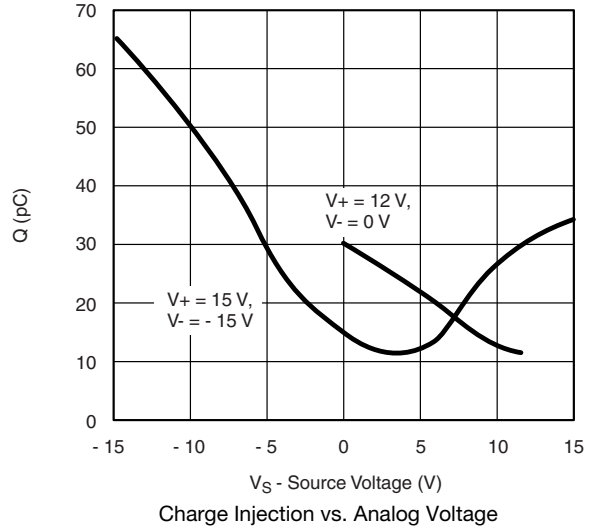
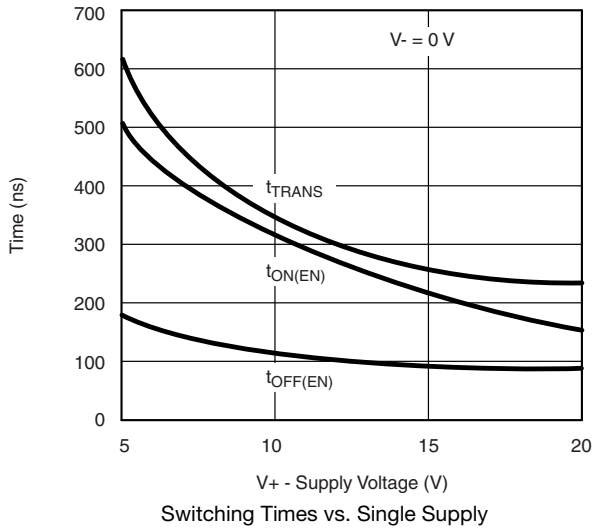
I_D, I_S Leakages vs. Temperature



Switching Times vs. Bipolar Supplies



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



SCHEMATIC DIAGRAM (Typical Channel)

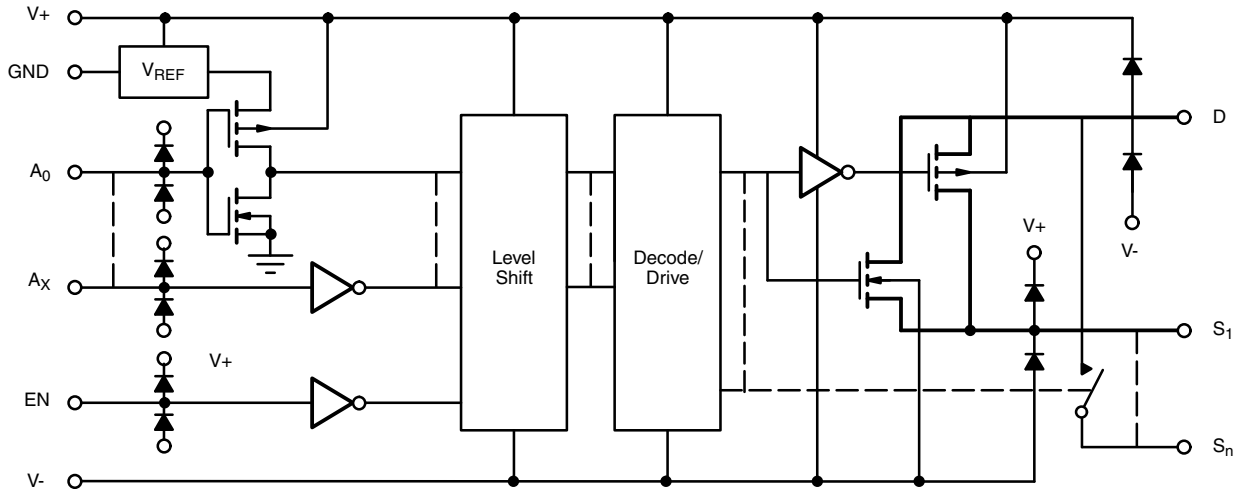
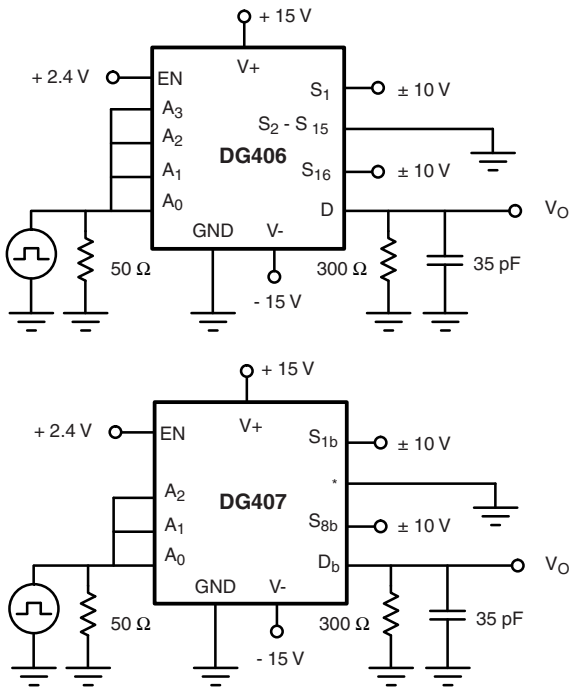


Fig. 1

TEST CIRCUITS



* = S_{1a} - S_{8a}, S_{2b} S_{±7b}, D_a

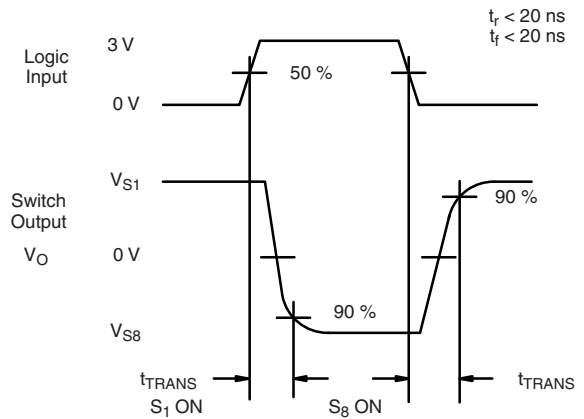


Fig. 2 - Transition Time

TEST CIRCUITS

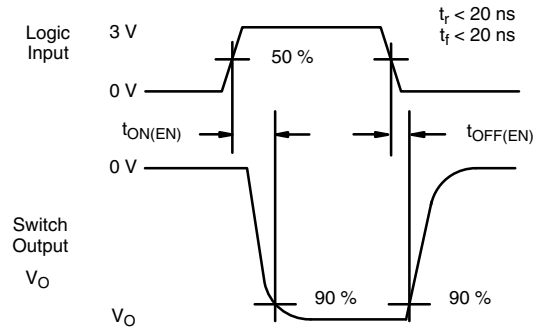
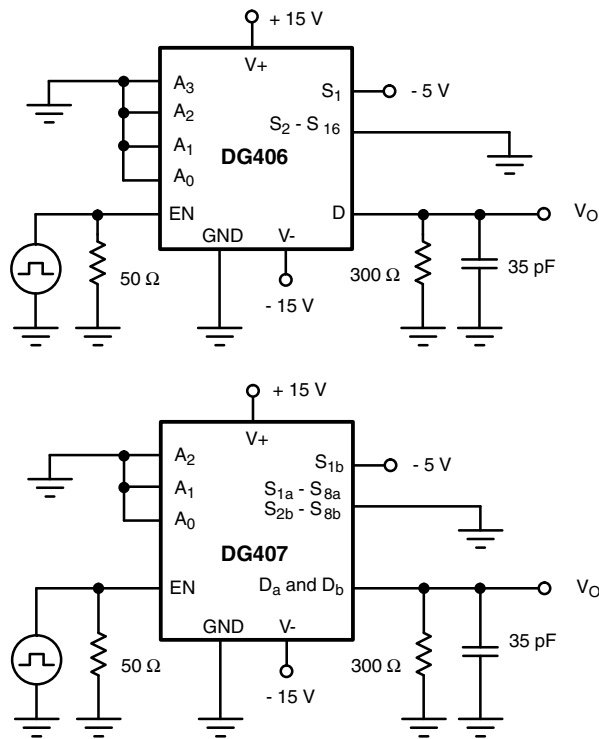


Fig. 3 - Enable Switching Time

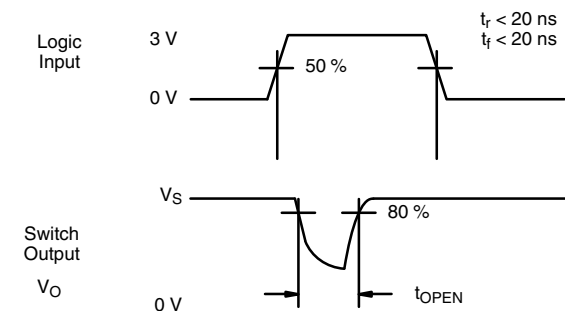
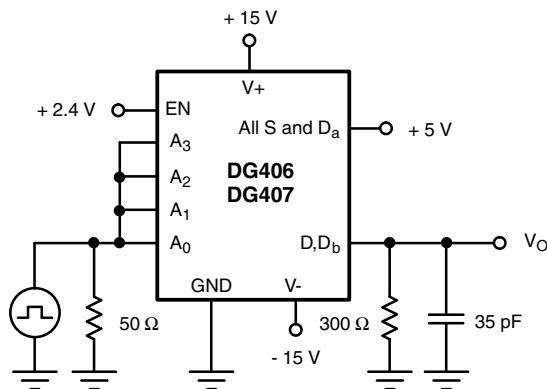


Fig. 4 - Break-Before-Make Interval

APPLICATIONS HINTS

Sampling speed is limited by two consecutive events: the transition time of the multiplexer, and the settling time of the sampled signal at the output.

t_{TRANS} is given on the data sheet. Settling time at the load depends on several parameters: $R_{DS(on)}$ of the multiplexer, source impedance, multiplexer and load capacitances, charge injection of the multiplexer and accuracy desired.

The settling time for the multiplexer alone can be derived from the model shown in figure 5. Assuming a low impedance signal source like that presented by an op amp or a buffer amplifier, the settling time of the RC network for a given accuracy is equal to $n\tau$:

% ACCURACY	# BITS	N
0.25	8	6
0.012	12	9
0.0017	15	11

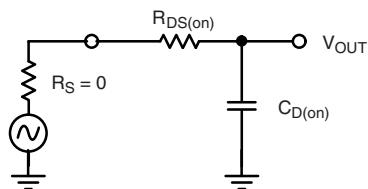


Fig. 5 - Simplified Model of One Multiplexer Channel

The maximum sampling frequency of the multiplexer is:

$$f_s = \frac{1}{N(t_{SETTLING} + t_{TRANS})} \quad (1)$$

where N = number of channels to scan

$$t_{SETTLING} = n\tau = n \times R_{DS(on)} \times C_{D(on)}$$

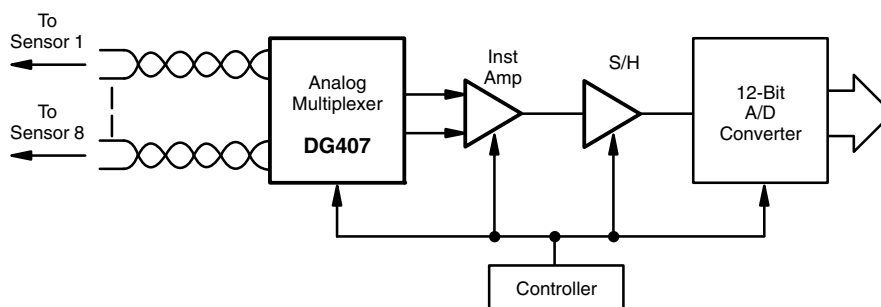


Fig. 6 - Measuring Low-Level Analog Signals is more accurate when using a Differential Multiplexing Technique

For the DG406 then, at room temp and for 12-bit accuracy, using the maximum limits:

$$f_s = \frac{1}{16(9 \times 100 \Omega \times 10^{-12} F) + 300 \times 10^{-12} s} \quad (2)$$

or

$$f_s = 694 \text{ kHz} \quad (3)$$

From the sampling theorem, to properly recover the original signal, the sampling frequency should be more than twice the maximum component frequency of the original signal. This assumes perfect bandlimiting. In a real application sampling at three to four times the filter cutoff frequency is a good practice.

Therefore from equation 2 above:

$$f_c = \frac{1}{4} \times f_s = 173 \text{ kHz} \quad (4)$$

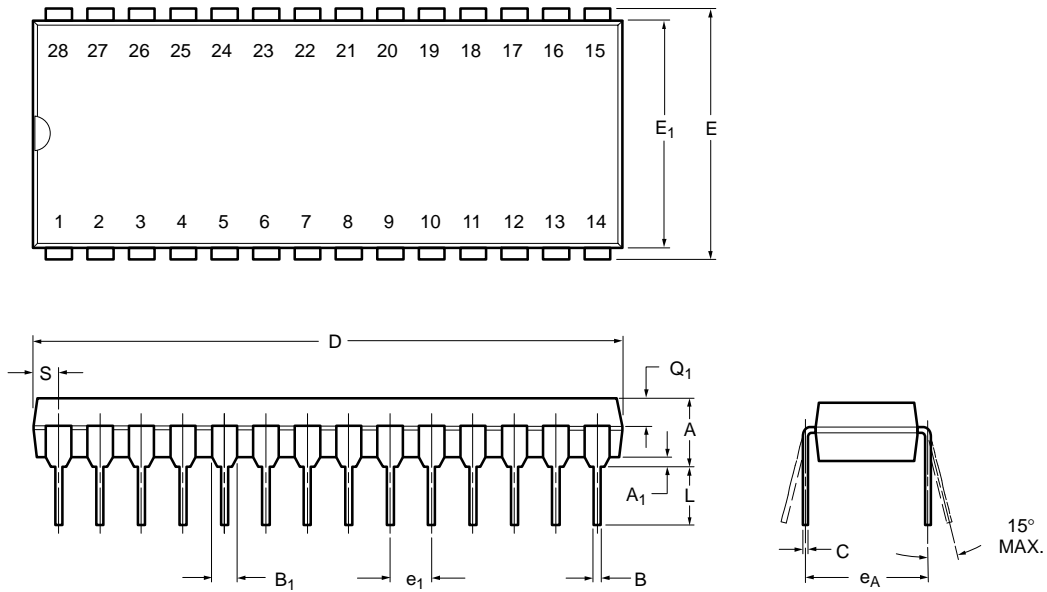
From this we can see that the DG406 can be used to sample 16 different signals whose maximum component frequency can be as high as 173 kHz. If for example, two channels are used to double sample the same incoming signal then its cutoff frequency can be doubled.

The block diagram shown in figure 6 illustrates a typical data acquisition front end suitable for low-level analog signals. Differential multiplexing of small signals is preferred since this method helps to reject any common mode noise. This is especially important when the sensors are located at a distance and it may eliminate the need for individual amplifiers. A low $R_{DS(on)}$, low leakage multiplexer like the DG407 helps to reduce measurement errors. The low power dissipation of the DG407 minimizes on-chip thermal gradients which can cause errors due to temperature mismatch along the parasitic thermocouple paths. Please refer to Application Note AN203 for additional information.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?70061.



PDIP: 28-LEAD

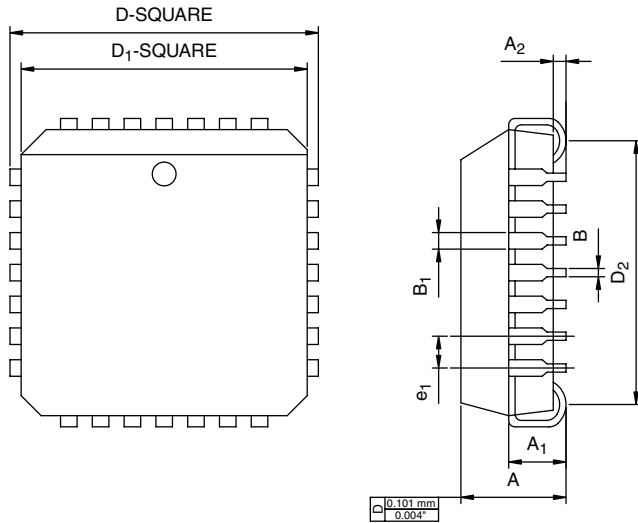


Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	2.29	5.08	0.090	0.200
A₁	0.39	1.77	0.015	0.070
B	0.38	0.56	0.015	0.022
B₁	0.89	1.65	0.035	0.065
C	0.204	0.30	0.008	0.012
D	35.10	39.70	1.380	1.565
E	15.24	15.88	0.600	0.625
E₁	13.21	14.73	0.520	0.580
e₁	2.29	2.79	0.090	0.110
e_A	14.99	15.49	0.590	0.610
L	2.60	5.08	0.100	0.200
Q₁	0.95	2.345	0.0375	0.0925
S	0.995	2.665	0.0375	0.105

ECN: S-03946—Rev. F, 09-Jul-01
DWG: 5488



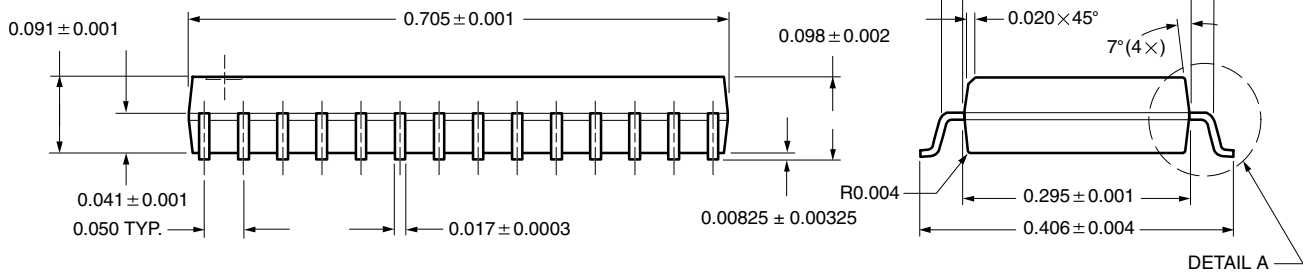
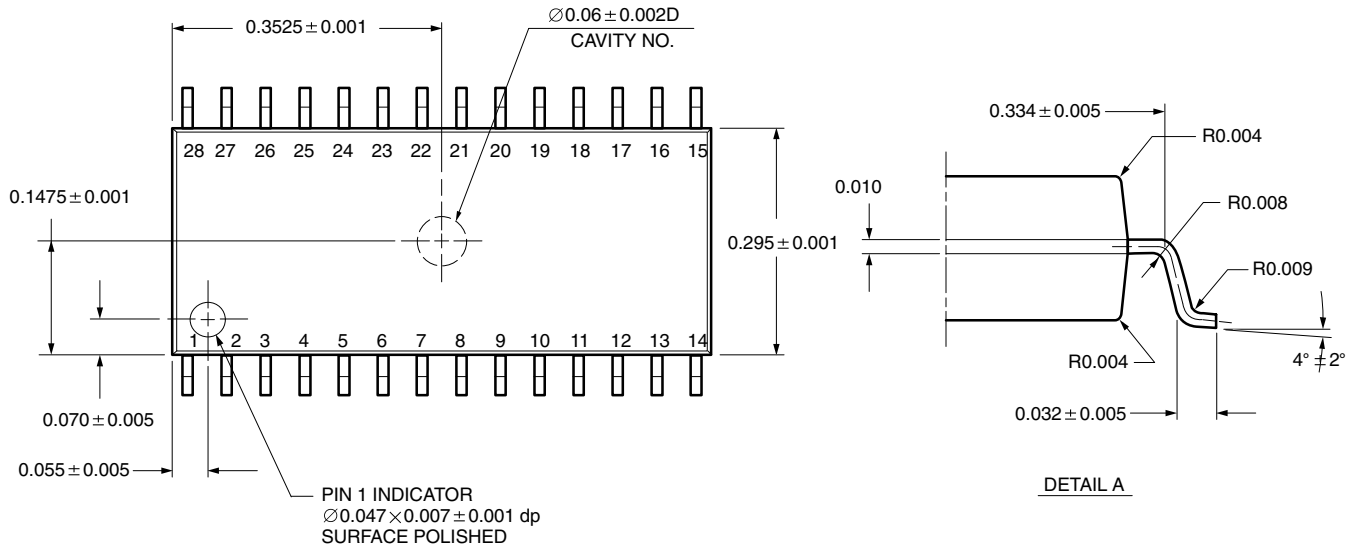
PLCC: 28-LEAD



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.20	4.57	0.165	0.180
A ₁	2.29	3.04	0.090	0.120
A ₂	0.51	-	0.020	-
B	0.331	0.553	0.013	0.021
B ₁	0.661	0.812	0.026	0.032
D	12.32	12.57	0.485	0.495
D ₁	11.430	11.582	0.450	0.456
D ₂	9.91	10.92	0.390	0.430
e ₁	1.27 BSC		0.050 BSC	
ECN: T09-0766-Rev. D, 28-Sep-09 DWG: 5491				



SOIC (WIDE-BODY): 28-LEADS



All Dimensions In Inches

ECN: E11-2209-Rev. D, 01-Aug-11
DWG: 5850



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.